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(12) **United States Design Patent**  
**Ochi et al.**

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(54) **INFORMATION STORAGE SEMICONDUCTOR ELEMENT**  
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(73) Assignee: **Matsushita Electric Industrial Co., Ltd.**, Osaka (JP)  
(\*\*) Term: **14 Years**

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(21) Appl. No.: **29/219,665**  
(22) Filed: **Dec. 20, 2004**  
(30) **Foreign Application Priority Data**  
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(51) **LOC (8) Cl.** ..... **13-03**  
(52) **U.S. Cl.** ..... **D13/182**  
(58) **Field of Classification Search** ..... D13/182;  
174/52.1; 257/98, 678, 680, 730; 361/684;  
365/145, 149, 212, 208; 438/64, 106  
See application file for complete search history.

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(57) **CLAIM**

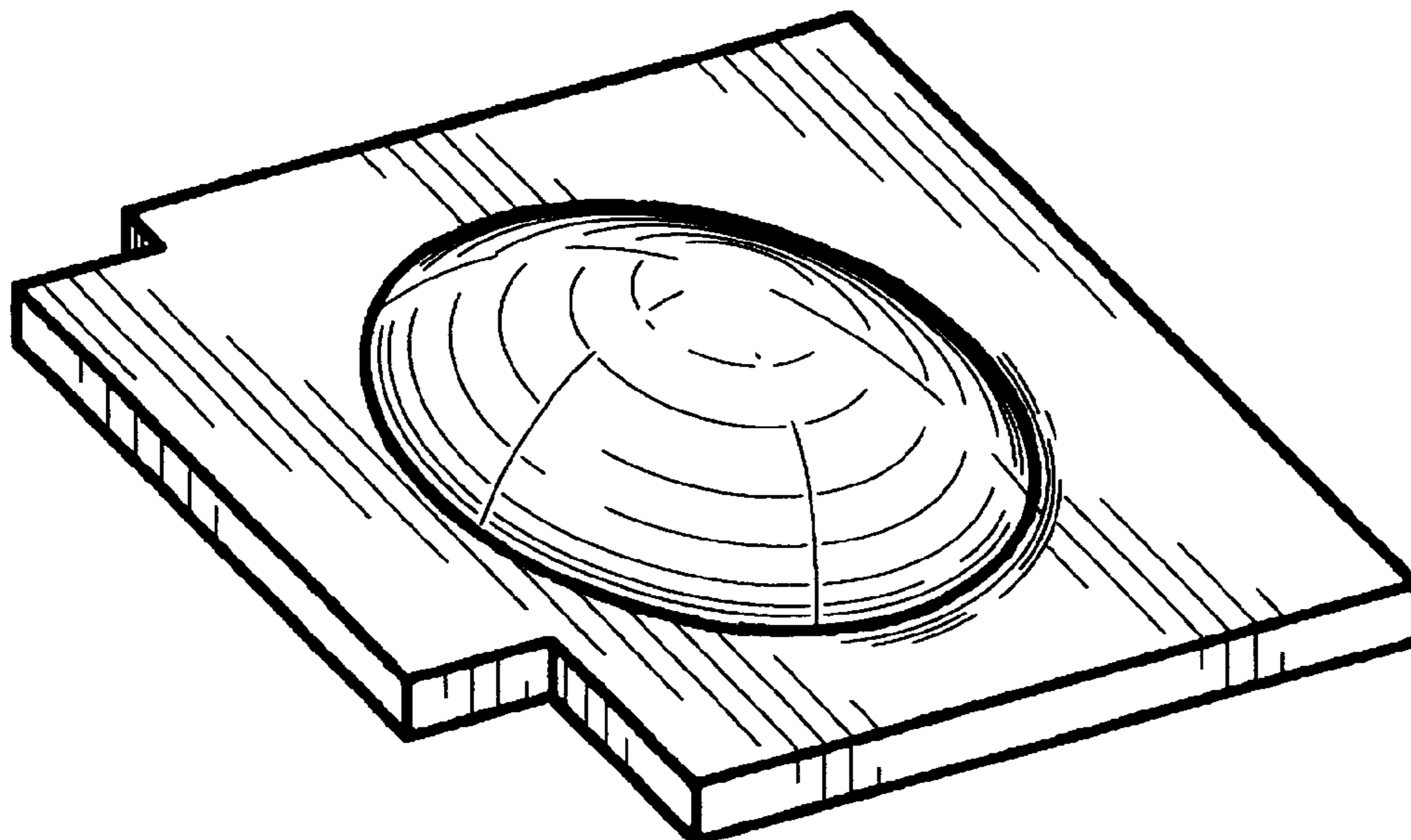
We claim the ornamental design for an information storage semiconductor element, as shown and described.

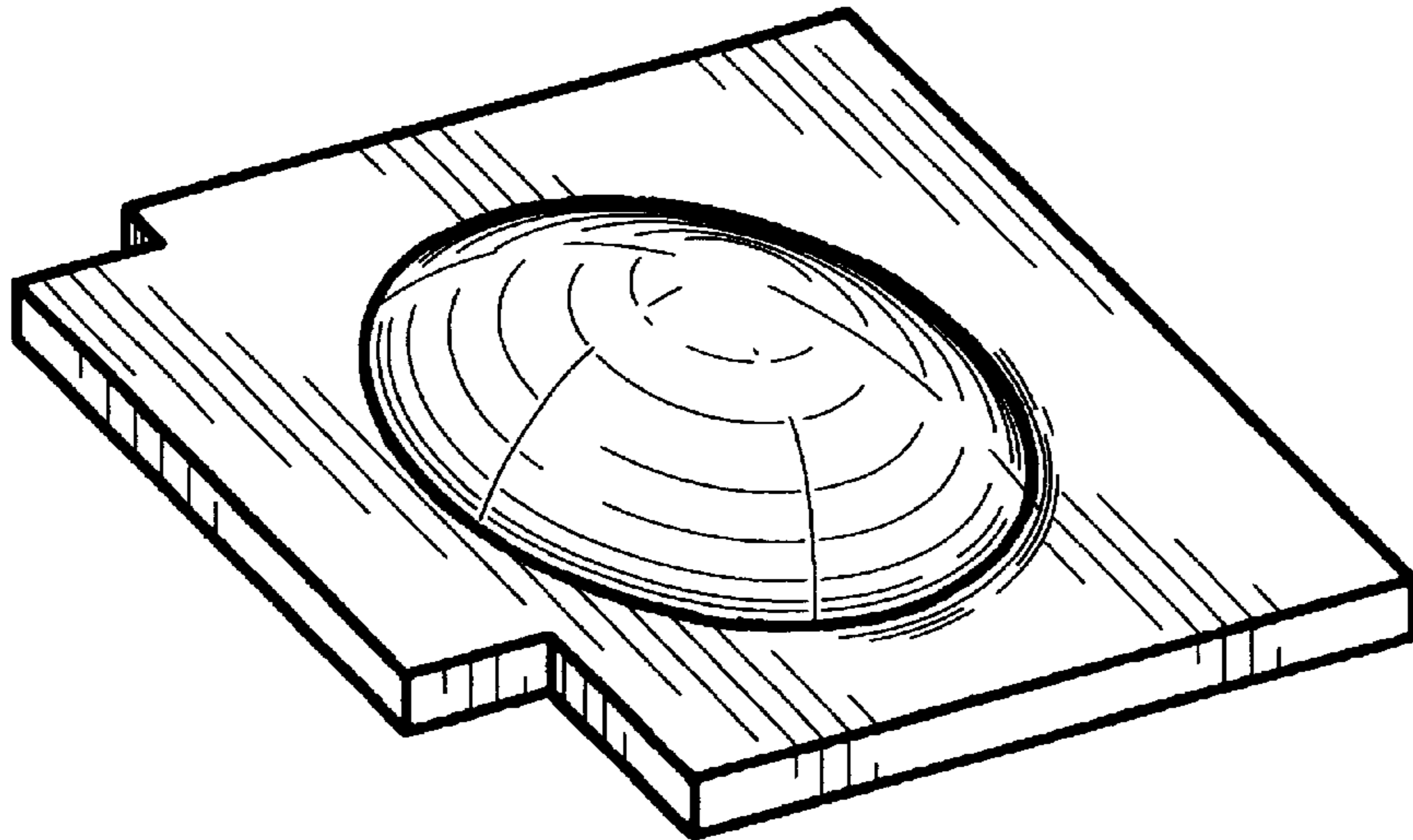
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**DESCRIPTION**

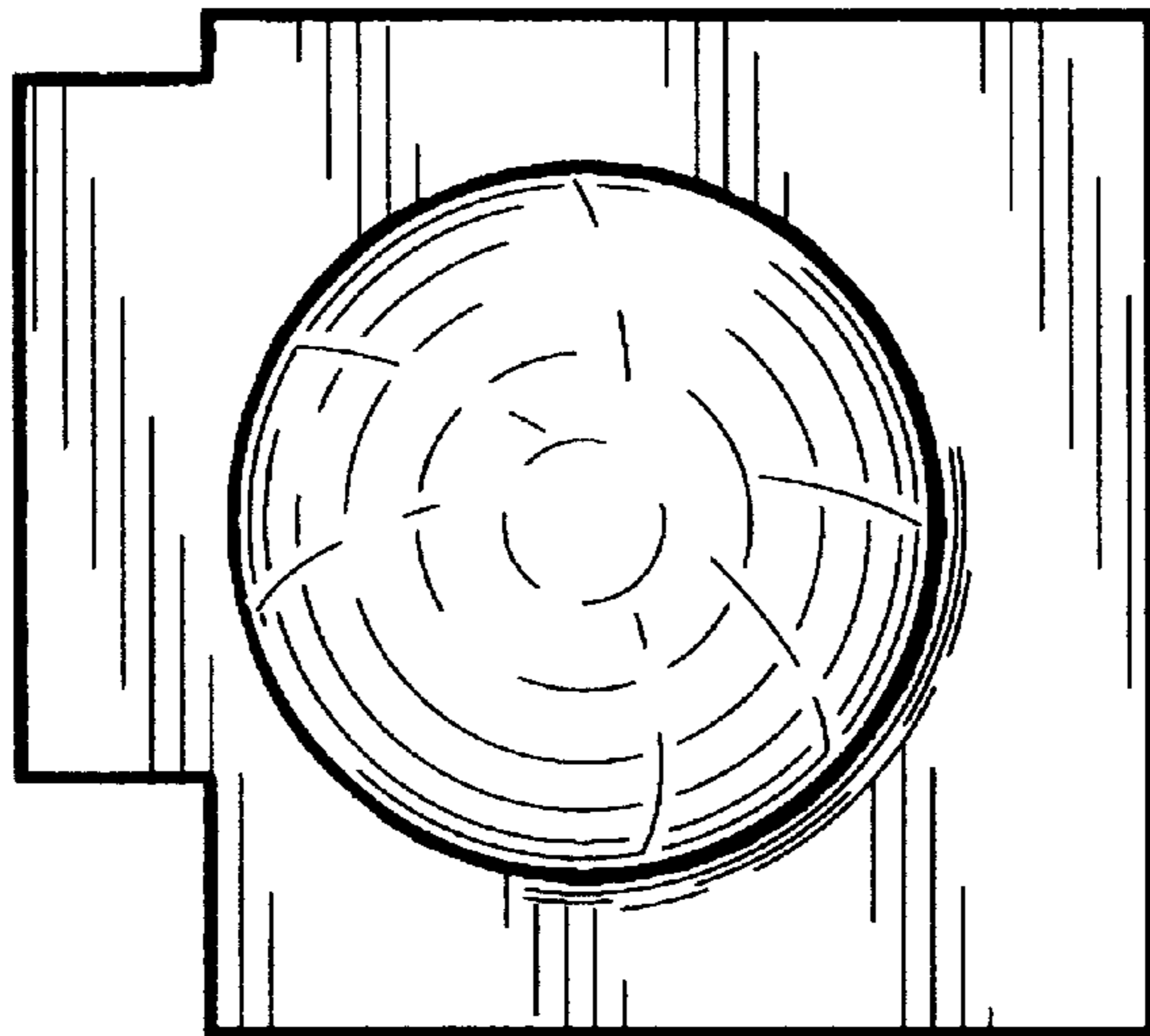
FIG. 1 is a top perspective view of an information storage semiconductor element of the present invention;  
FIG. 2 is a top view thereof;  
FIG. 3 is a bottom view thereof;  
FIG. 4 is a front view thereof;  
FIG. 5 is a rear view thereof; and,  
FIG. 6 is a first side view thereof, wherein the second side view is a mirror image thereof.

**1 Claim, 6 Drawing Sheets**

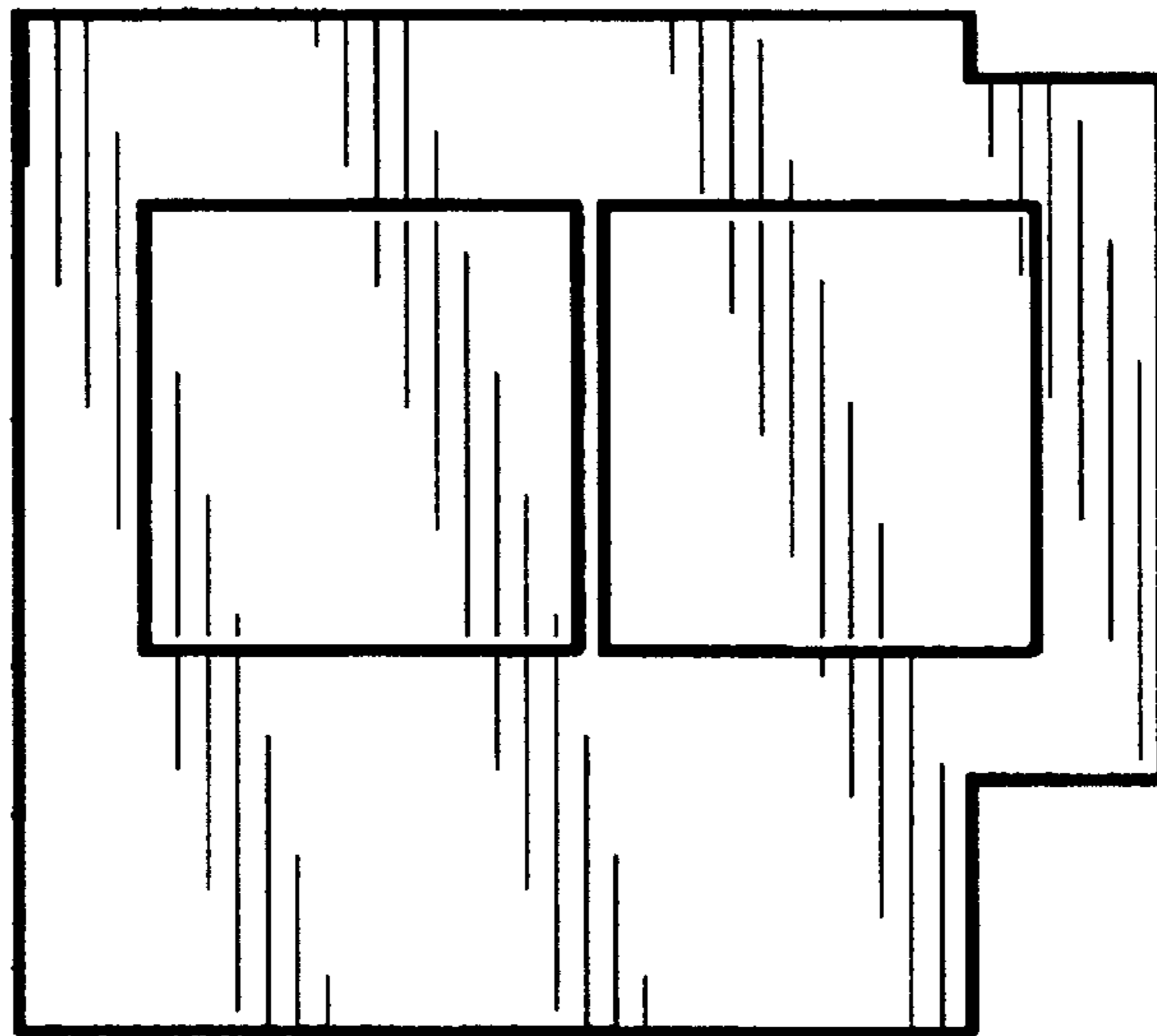




**FIG. 1**



**FIG. 2**



**FIG. 3**

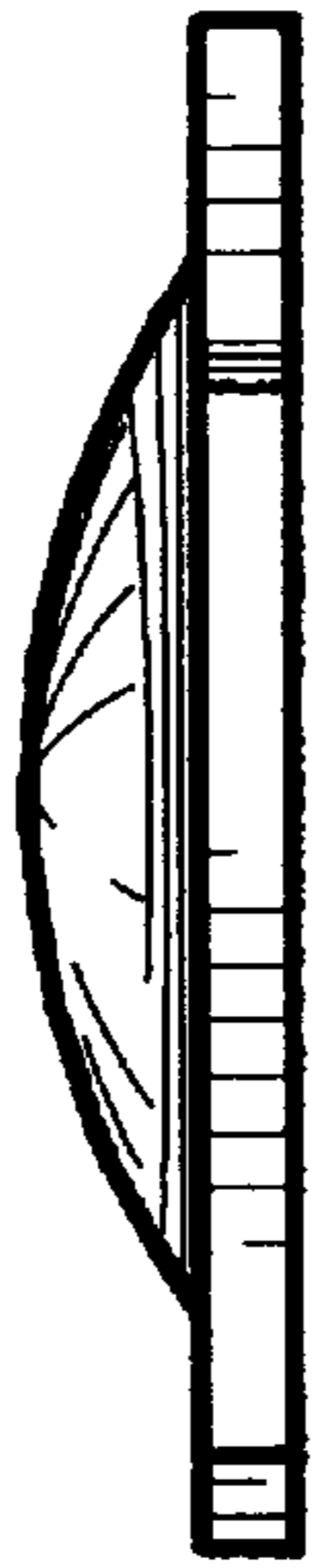
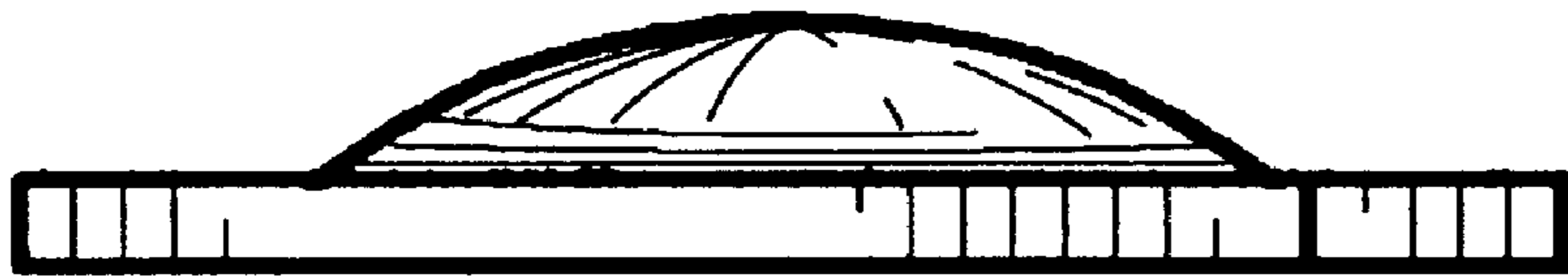


FIG. 4



FIG. 5



**FIG. 6**